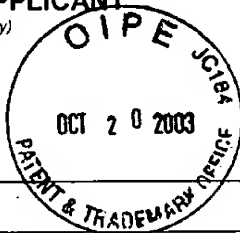


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Application Number	09/945507
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2824
Examiner Name	Dinh, Son

Sheet 1 of 4

Attorney Docket No: 1303.014US1

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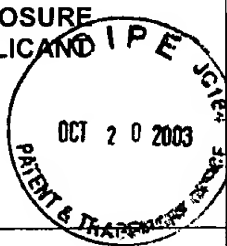
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Application Number	09/945597
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
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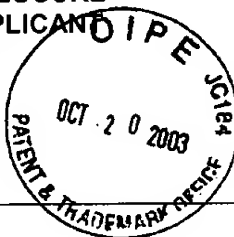
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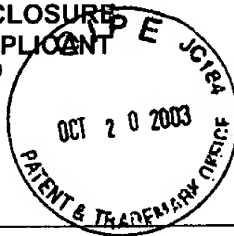
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Examiner Name	Dinh, SON

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